

Image

2812

Docket: TSMC 98 - 262CC

S/N: 09/325,951



Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Serial No.: 09/325,951

Filed: 06/04/1999

Inventor: Min-Hsiung Chiang

Title: Method For Forming High Purity Silicon Oxide Field  
Oxide Isolation Region

Group Art Unit: 2812

Examiner: Pompey, R. E.

Attorney Docket: TSMC 98 - 262CC

### RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the office action dated 01/12/04, please consider the  
following remarks:

### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the  
United States Postal Service as first class mail in an envelope addressed to:

Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on \_\_\_\_\_

April 12, 2004.

Signature/Date

4/12/04

Stephen B. Ackerman  
Reg. No. 37,761

**Charge to Deposit Account**

The Commissioner is hereby authorized to charge payment of the fee of \$\_\_\_\_\_ associated with this communication, or credit any overpayment, to Deposit Account No. 19-0033. The Commissioner is also authorized to charge any additional fee under 37 CFR §1.16 and 1.17 to this Deposit Account. A duplicate copy of this sheet is enclosed. The Commissioner is hereby authorized to charge payment of any additional fees involved with added Claims and the like to Deposit Account No. 19-0033.

Respectively submitted,

\_\_\_\_\_  
Date

\_\_\_\_\_  
George O. Saile; or  
Stephen B. Ackerman